Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for full-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half–wave silicon gate–controlled, solid–state devices are needed.

Features

- Glass Passivated Junctions and Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 50 Volts
- This is a Pb–Free Device

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

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Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T _J = 25 to 100°C, Sine Wave, 50 to 60 Hz; Gate Open)	V _{DRM,} V _{RRM}	50	V
On-State RMS Current (180° Conduction Angles; T _C = 75°C)	I _{T(RMS)}	8.0	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _C = 75°C)	I _{TSM}	90	A
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	34	A ² s
Forward Peak Gate Power (Pulse Width = 10 μs, T _C = 70°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, T _C = 70°C)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width = 10 μs, T _C = 70°C)	I _{GM}	2.0	A
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Normended Operating Conditions may affect device reliability.
V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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	PIN ASSIGNMENT
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

Device	Package	Shipping
C122F1G	TO220AB (Pb-Free)	500 Units / Box

C122F1G

THERMAL CHARACTERISTICS

Characteristic				Symbol	Max	Unit
Thermal Resistance, Junction-to-Case				$R_{\theta JC}$	1.8	°C/W
Thermal Resistance, Junction-to-Ambient		$R_{\theta JA}$	62.5	°C/W		
Maximum Lead Temperature for Soldering Purposes 1/8 in. from Case for 10 Seconds		TL	260	°C		
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless	otherwise noted.)				
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM} , Gate Open)	T _C = 25°C T _C = 125°C	I _{DRM} , I _{RRM}	-		10 0.5	μA mA
ON CHARACTERISTICS						
Peak On–State Voltage (Note 2) $(I_{TM} = 16 \text{ A Peak}, T_C = 25^{\circ}C)$		V _{TM}	-	-	1.83	V
Gate Trigger Current (Continuous dc) $(V_{AK} = 12 \text{ V}, \text{ R}_L = 100 \Omega)$	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	I _{GT}	-		25 40	mA
Gate Trigger Voltage (Continuous dc) $(V_{AK} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	V _{GT}			1.5 2.0	V
Gate Non-Trigger Voltage (Continuous dc) $(V_{AK} = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_C = 125^{\circ}\text{C})$		V _{GD}	0.2	-	_	V
Holding Current (V _{AK} = 12 Vdc, Initiating Current = 200 mA, Gate Open)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	Ι _Η			30 60	mA
Turn-Of f Time (V_D = Rated V_{DRM}) (I_{TM} = 8 A, I_R = 8 A)		tq	-	50	-	μs
DYNAMIC CHARACTERISTICS						
Critical Rate-of-Rise of Off-State Voltage (V _{AK} = Rated V _{DRM} , Exponential Waveform, Gate Open	, T _C = 100°C)	dv/dt	-	50	_	V/μs

2. Pulse Test: Pulse Width \leq 1 ms, Duty Cycle \leq 2%.

C122F1G

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
Ι _Η	Holding Current







I_{T(AV)}, AVERAGE ON-STATE CURRENT (AMPERES) Figure 3. Maximum Power Dissipation (Half-Wave)







(Full-Wave)

 $\mathsf{P}(\mathsf{AU})_{\mathsf{r}}$ AVERAGE ON-STATE POWER DISSIPATION (WATTS)

12

10

8

6

0

C122F1G

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE AA



	VED.			S ARE
	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
Г	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI

> STYLE 3: PIN 1. CATHODE

2. ANODE

3. GATE

4. ANODE

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